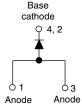
8EWS..SPbF High Voltage Series

Vishay Semiconductors

Surface Mountable Input Rectifier Diode, 8 A



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υ-	PА	N

PRODUCT SUMMARY								
Package	D-PAK (TO-252AA)							
$I_{F(AV)}$ at $T_C = 116$ °C	8 A							
V_{R}	800 V, 1200 V							
V _F at I _F	1.1 V							
I _{FSM}	200 A							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



ROHS

DESCRIPTION

The 8EWS..SPbF rectifier High Voltage Series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.

The **high reverse voltage** range available allows design of input stage primary rectification with **outstanding voltage surge** capability.

Typical applications are in input rectification and these products are designed to be used with Vishay Semiconductors switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	1.2	1.6						
Aluminum IMS, R _{thCA} = 15 °C/W	2.5	2.8	Α					
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	5.5	6.5						

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I _{F(AV)}	Sinusoidal waveform at T _C = 116 °C	8	А					
V _{RRM}		800/1200	V					
I _{FSM}		200	А					
V _F	8 A, T _J = 25 °C	1.10	V					
TJ		- 55 to 150	°C					

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA					
8EWS08SPbF	800	900	0.5					
8EWS12SPbF	1200	1300	0.5					

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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum average forward current	I _{F(AV)}	T _C = 105 °C, 180° conduction half sine wave	10					
Maximum peak one cycle		10 ms sine pulse, rated V _{RRM} applied	170	Α				
non-repetitive surge current	I _{FSM}	10 ms sine pulse, no voltage reapplied	200					
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	130	A ² s				
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	145	A-5				
Maximum I²√t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied	1450	A²√s				

ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS					
Maximum forward voltage drop	V_{FM}	8 A, T _J = 25 °C		1.1	V			
Forward slope resistance	r _t	T _{.1} = 150 °C	20	mΩ				
Threshold voltage	V _{F(TO)}	1j = 130 C	0.82	V				
Mariana		T _J = 25 °C	V - Batad V	0.05	A			
Maximum reverse leakage current	IRM	T _J = 150 °C	V _R = Rated V _{RRM}	0.50	mA			

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55 to 150	°C	
Soldering temperature	T _S 240		240		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2.5	°C/W	
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA (1)}		62	C/VV	
A navavimata waight			1	g	
Approximate weight			0.03	OZ.	
Marking device		Case style D-PAK (TO-252AA)	8EWS	S12S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

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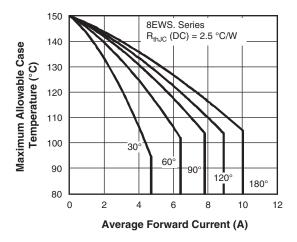


Fig. 1 - Current Rating Characteristics

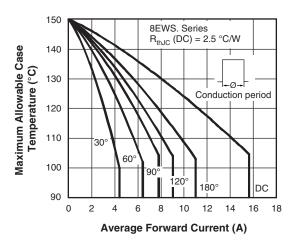


Fig. 2 - Current Rating Characteristics

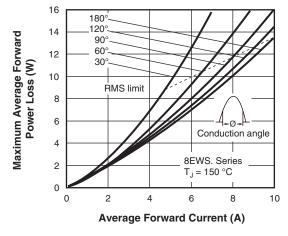


Fig. 3 - Forward Power Loss Characteristics

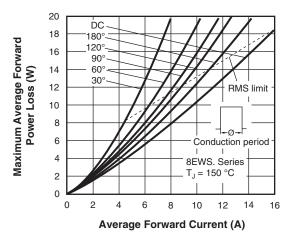


Fig. 4 - Forward Power Loss Characteristics

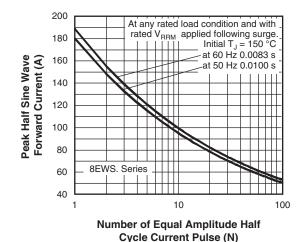


Fig. 5 - Maximum Non-Repetitive Surge Current

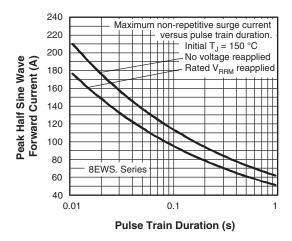


Fig. 6 - Maximum Non-Repetitive Surge Current

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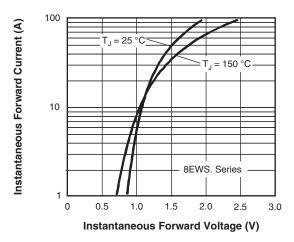


Fig. 7 - Forward Voltage Drop Characteristics

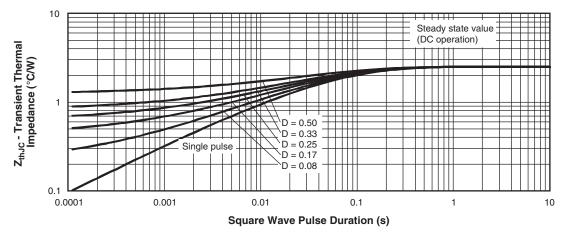


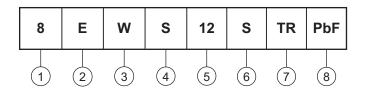
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



Current rating (8 = 8 A)

Circuit configuration:

E = Single diode

3 Package:

W = D-PAK

4 Type of silicon:

S = Standard recovery rectifier

08 = 800 V

5 Voltage ratings 12 = 1200 V

6 S = Surface mountable

• TR = Tape and reel

• TRR = Tape and reel (right oriented)

• TRL = Tape and reel (left oriented)

8 PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95016					
Part marking information	www.vishay.com/doc?95059					
Packaging information	www.vishay.com/doc?95033					



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NOTES

3

2

MAX.

0.410

0.070

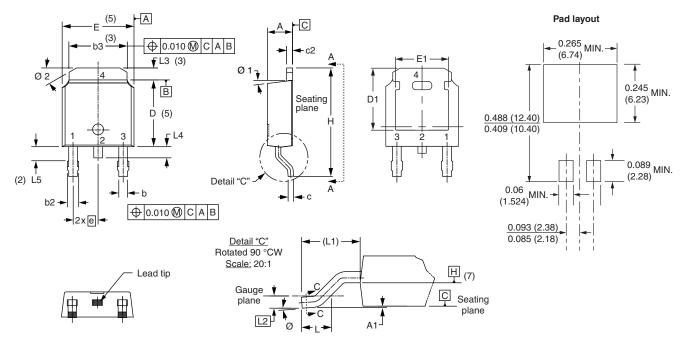
0.050

0.040

0.060

D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



Ī	SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES			
		MIN.	MAX.	MIN.	MAX.	NOTES		STWIBUL	MIN.	MAX.	MIN.	MAX	
ſ	Α	2.18	2.39	0.086	0.094	e 2.29 BSC 0.090		e 2.29 BSC		2.29 BSC		BSC	
ſ	A1	-	0.13		0.005			Н	9.40	10.41	0.370	0.41	
Ī	b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.07	
Ī	b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
ſ	b3	4.95	5.46	0.195	0.215	3		L2	0.51	0.51 BSC		0.020 BSC	
Ī	С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.05	
Ī	c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.04	
ſ	D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.06	
Ī	D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
ſ	Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
Ī	E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- Lead dimension uncontrolled in L5
- Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- Outline conforms to JEDEC outline TO-252AA



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